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Signature of Metallic Behavior in the Metal-Organic Frameworks M_3 (hexaiminobenzene)₂ (M = Ni, Cu)

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Supporting Information Placeholder

ABSTRACT: The two-dimensionally connected metal-organic frameworks (MOFs) $Ni_3(HIB)_2$ and $Cu_3(HIB)_2$ (HIB = hexaiminobenzene) are bulk electrical conductors and exhibit ultraviolet-photoelectron spectroscopy (UPS) signatures expected of metallic solids. Electronic band structure calculations confirm that in both materials the Fermi energy lies in a partially filled delocalized band. Together with additional structural characterization and microscopy data, these results represent the first report of metallic behavior and permanent porosity coexisting within a metal-organic framework.

Recent progress in the synthesis of electrically conductive metalorganic frameworks (MOFs) has enabled applications that were previously thought impractical for this traditionally insulating set of materials.¹ Examples include the use of neat MOFs as active electrodes in electrocatalysis, ^{2,3} batteries, ^{4,5} chemiresistive sensors, ^{6,7} thermoelectric devices, ⁸ supercapacitors, ⁹ electrochromic devices, ¹⁰ and field effect transistors. ¹¹ The high porosity and surface area of these materials offer new functionalities and opportunities, especially in sensing and supercapacitors, where a large amount of host-guest interaction sites are critical. ^{6,7,9} Many of these applications are served better by semiconducting MOFs, others would see considerable improvements if the MOFs were metallic. However, there are thus far no examples of metallic MOFs. Demonstrating metallic behavior remains an important challenge of fundamental interest. Along this line, the only materials in this class that exhibit a bulk conductivity greater than 10 S/m at room temperature are $Ni_3(2,3,6,7,10,11$ -hexaiminotripheny $(Ni_3(HITP)_2)$, 12 $Ni_3(benzenehexathiol)_2$ $(Ni_3(BHT)_2)$, 13 $Ni_3(2,3,6,7,10,11$ -hexaiminotriphenylene)₂ Cu₃(benzenehexathiol)₂ (Cu₃(BHT)₂). ¹⁴ All three belong to a subclass of hexagonal layered structures wherein trigonal organic ligands and square-planar mononuclear metal nodes define two-dimensional (2D) sheets whose electronic structure enables excellent electron delocalization through continuous conjugation.

Relevantly, theoretical studies of these 2D materials predicted that some should behave as bulk metals, ^{13,15–17} yet experimental evidence for metallic behavior in these remains elusive. 13 We surmised that replacing 2,3,6,7,10,11-hexaiminotriphenylene (HITP) by the smaller hexaiminobenzene (HIB) would reduce the distance and provide better overlap between the electronic wavefunctions of metals/ligands in Ni₃(hexaiminobenzene)₂ (Ni₃(HIB)₂), leading possibly to metallicity. However, recently reported field effect transistors (FETs) made from films of M₃(HIB)₂ (M = Ni, Co, Cu) exhibited responses characteristic of insulators or materials with very low conductance, at best. 18 We contended that this surprisingly insulating behavior was due to the severe disorder and poor crystallinity of the films, as evidenced also by selected area electron diffraction (SAED), and that more crystalline samples would reveal different information about the intrinsic properties of these materials. Accordingly, on the premise that HIB-based frameworks continue to be ideal candidates for metallic MOFs, we set out to devise new synthetic pathways for accessing high quality and crystalline samples of these materials and explore their electrical properties.

Here, we show that crystalline $Ni_3(HIB)_2$ and $Cu_3(HIB)_2$, characterized by X-ray diffraction, spectroscopic analysis, and high resolution transmission electron microscopy (HRTEM), are indeed excellent conductors, with pellet conductivities averaging approximately $1000 \, \text{S/m}$ at $300 \, \text{K}$ and under vacuum. Significantly, ultraviolet-photoelectron spectroscopy (UPS) and electronic band structure calculations evidence intrinsic metallic behavior in both materials.

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Scheme 1. Synthesis of Ni₃(HIB)₂ and Cu₃(HIB)₂.

Black microcrystalline samples of $M_3(HIB)_2$ (M = Ni, Cu) were isolated from reactions of hexaaminobenzene trihydrochloride (HAB·3HCl) with ammoniacal solutions of Ni(NO₃)₂·6H₂O or CuSO₄·5H₂O in mixtures of water and dimethylsulfoxide heated at 60 °C in air for two hours. The presence of O₂ is essential for the isolation of crystalline materials; the absence of air yields only amorphous grey powders. Scanning electron microscopy (SEM) showed that the products consist of irregularly shaped nanoparticles smaller than 100 nm (Figure S3). Inspection of the M(2p) and N(1s) regions of the high resolution X-ray photoelectron spectra (XPS, Figures S4 and S5) evidenced a chemical environments consistent with square planar metal ions and anilinic N atoms in both materials. Additional extra-framework M²⁺ or NH₄⁺ ions, the only possible charge-balancing cations for a potentially negatively charged MOF would appear at different regions in the XPS; their absence confirms the neutral state of M₃(HIB)₂.

Thermogravimetric analysis (TGA) revealed that both $\rm Ni_3(HIB)_2$ and $\rm Cu_3(HIB)_2$ desolvate above 100 °C and likely decompose above 200 °C, as evidenced by the more pronounced weight losses above this temperature (Figure S6). Evacuation at 120 °C under dynamic vacuum for 24 h followed by $\rm N_2$ sorption analysis reavealed type II isotherms with uptakes of 82 and 65 cm³/g at 77 K and apparent Brunauer–Emmett–Teller (BET) surface areas of 152 m²/g and 114 m²/g for $\rm Ni_3(HIB)_2$ and $\rm Cu_3(HIB)_2$, respectively (Figure S7). These values are in line with those of other 2D materials exhibiting similar pore sizes (vide infra).

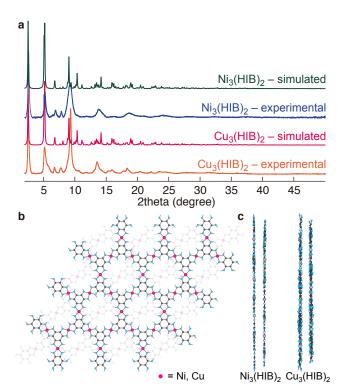


Figure 1. (a) Powder X-ray diffraction patterns. (b,c) Calculated structures of $M_3(HIB)_2$.

Synchrotron powder X-ray diffraction (PXRD) confirmed a high degree of crystallinity: both materials exhibit prominent diffraction peaks at $2\theta = 2.54^{\circ}$, 5.18° , 6.81° , 8.10° , 9.07° , 14.27° , and 18.97° (Figures 1, S8 and S9). Indexing of these peaks revealed hexagonal unit cells with lattice parameters a = 13.5(2) Å and c = 3.3(1) Å. To determine the precise interlayer stacking sequence, we performed Ni and Cu K-edge extended X-ray absorption fine structure (EXAFS) analysis. Ni···Ni and Cu···Cu scattering paths at R = 3.60 ± 0.09 Å and R = 3.33 ± 0.10 Å were required to fit the EXAFS spectra of Ni₃(HIB)₂ and Cu₃(HIB)₂, respectively (Figure S10). Both M···M distances determined by XAS analysis exceed the interlayer distance observed by PXRD, suggesting that the 2D layers are not perfectly eclipsed and that significant (ab) shifting occurs in both materials between neighboring layers. Taken together, the PXRD and XAS data give structural models where neighboring layers are shifted by approximately one quarter cell along one edge of the hexagonal unit cell, thereby lowering the symmetry to orthorhombic. Indeed, Le Bail fitting of the PXRD patterns of the two materials gave best fits for space groups Cmcm and C2221 for Ni₃(HIB)₂ and Cu₃(HIB)₂, respectively (Figure S11), with otherwise identical unit cell parameters a = 13.5(2) Å, b = 23.3(5) Å and c = 6.6(1) Å.

To understand the difference in symmetry between the Ni and Cu materials, we computed optimized geometries for individual 2D sheets using density functional theory (DFT) (Figure S12). This revealed hexagonal lattice constants of 13.48 Å, in agreement with the experimental values. It also revealed that the local symmetry of the Ni²⁺ ions is strictly D_{4h}, giving rise to completely planar Ni₃(HIB)₂ monolayers, whereas CuN₄ units buckle out-of-plane and give rise to overall buckled 2D layers in Cu₃(HIB)₂ (Figures 1c and S12). We therefore attribute the lack of mirror symmetry in Cu₃(HIB)₂ to the local coordination environment of the Cu²⁺ ions (Figures 1c and S12).

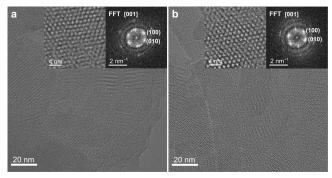


Figure 2. HRTEM image of (a) Ni₃(HIB)₂ and (b) Cu₃(HIB)₂ taken at 300 kV. Insets are high magnification HRTEM images (left) and the corresponding FFT analysis (right).

HRTEM provided further evidence of two-dimensional long-range order in $M_3(HIB)_2$. Most notably, fast Fourier transform (FFT) analysis of the images in Figure 2 reavealed honeycomb lattices with a lattice parameter a=13.5 Å, in excellent agreement with the values obtained from PXRD analysis and DFT computations. Intriguingly, our microscopy and structural data contrasts with that previously reported for these materials. In particular, it suggests a higher degree of crystallinity and potentially a different structure for our materials, which encouraged us to investigate the electronic properties of $M_3(HIB)_2$ samples as synthesized here.

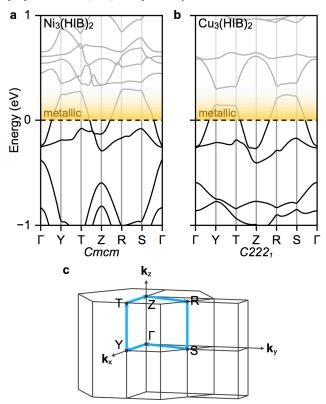


Figure 3. (a,b) Calculated electronic band structure of bulk Ni₃(HIB)₂ and Cu₃(HIB)₂, respectively. (c) The corresponding first Brillouin zone and high-symmetry k-points.

Importantly, DFT electronic band structure calculations suggested that both monolayer and bulk $M_3(HIB)_2$ should be metallic. Monolayers of both Ni and Cu MOFs exhibit electronic band structures featuring two wide bands forming a Dirac cone at the K point, reminiscent of the classic Kagome bands (Figure S13). ¹⁹ The Dirac bands cross the Fermi level in both Γ –K and Γ –M directions and have wide band dispersions of approximately 0.8 eV. The projected

density of states exhibits considerable contributions from the metal, C, and N orbitals at the Fermi level, confirming the high degree of in-plane π -conjugation expected for these materials.

The electronic band structures of bulk orthorhombic $M_3(HIB)_2$ plotted along the high symmetry points in the 1st Brillouin zone are shown in Figure 3 and Figure S14. Salient features include bands crossing the Fermi level in the in-plane Γ -Y, T-Z, Z-R, and Γ -S directions in both materials, which indicates the metallic character of both solids. Notably, because no bands cross the Fermi level in the out-of-plane directions (Y-T and R-S), the bulk materials are expected to be metallic only in the *ab* directions and semiconducting in the *c* direction.

The bulk electrical properties of $M_3(HIB)_2$ were determined from pelletized samples of the two materials, obtained by pressing powders at approximately 1 GPa. Upon degassing under dynamic vacuum ($\sim 1 \times 10^{-5}$ torr) at 150 °C, the pellets were imaged with SEM, which revealed small particles with prominent grain boundaries and voids (Figure S15). The electrical conductivity of the pellets, measured by the van der Pauw method (Figure S16) under vacuum and in the dark²⁰ was 800 S/m for Ni₃(HIB)₂ and 1300 S/m in Cu₃(HIB)₂ at 300 K. These are among the highest values observed for MOFs, and compare favorably even with the more relevant subset of electrically conducting 2D MOFs.¹

Although a signature of bulk metallic behavior is thermally deactivated transport,²¹ temperature-dependence conductivity measurements revealed that electrical transport in both Ni₃(HIB)₂ and Cu₃(HIB)₂ correlates positively with temperature. Indeed, the electrical conductivity in polycrystalline pellets of both MOFs increases linearly as the temperature increases from 200 K to 420 K (Figure 4a). PXRD confirmed that no structural transitions occur in this temperature range (Figure S17). We attribute the observed thermally activated transport, more characteristic of semiconducting rather than metallic behavior, to interparticle rather than intraparticle (i.e. intrinsic) transport. In other words, thermally-activated hopping over grain boundaries (i.e. interparticle transport) dominates the temperature dependence of conductivity in the bulk polycrystalline pellets, giving rise to apparent semiconducting behavior in otherwise intrinsically metallic solids. Indeed, this behavior is well documented for granular metals where inter-grain charge hopping mediates charge transport (Figure S18).²² Further complicating the interpretation of the bulk conductivity of M₃(HIB)₂ is the bimodal transport expected from DFT band structure calculations: metallic in the plane of the MOF sheets, but semiconducting normal to the 2D sheets (vide supra). Because the orientation of particles in the pellets is random, both in-plane and out-of-plane charge transport contribute to bulk conductivity, the latter in line with the observed temperature dependence.

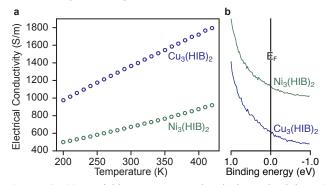


Figure 4. (a) Variable-temperature electrical conductivity of pressed pellets of M₃(HIB)₂ measured by the van der Pauw method under vacuum. (b) UPS of M₃(HIB)₂ acquired at 300 K.

Experimental confirmation of the metallic nature of both MOFs came from UPS, which informs on the intrinsic properties of even polycrystalline samples by measuring the density of states near the Fermi level. Grazing incident wide-angle X-ray scattering (GIWAXS) of Ni₃(HIB)₂ and Cu₃(HIB)₂ films prepared on highly-doped silicon (Figure S19), as required for UPS measurements, confirmed the identity of the two MOFs and showed that they preferably orient with a typical face-on packing mode where the 2D sheets are parallel to the silicon substrate (Figure S20).²³ The UPS measurements at 300 K revealed Fermi edges for both Ni₃(HIB)₂ and Cu₃(HIB)₂ (Figure 4b and S21), which are indicative of electronic bands crossing the Fermi level, and are strong evidence for metallic behavior in M₃(HIB)₂. ^{13,24}

In conclusion, we show that reaction of hexaaminobenzene with Ni²⁺ or Cu²⁺ under carefully controlled conditions gives rise to porous crystalline materials with bulk electrical conductivities exceeding 800 S/m. UPS measurements and DFT computational studies evidenced rare metallic behavior in MOFs, a class of notoriously insulating materials. Most importantly, we demonstrate for the first time that metallic behavior and porosity are compatible in these materials. These results encourage further fundamental physical studies and advanced electronic applications, which continue to depend critically on the development of techniques to grow and study single crystals of 2D MOFs, an area of current efforts in our group.

ASSOCIATED CONTENT

Supporting Information

Additional experimental details and characterization data. This material is available free of charge via the Internet at http://pubs.acs.org.

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Notes

The authors declare no competing financial interests.

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